

ABSTRACT OF THE DISCLOSURE

Power semiconductor switching devices, power converters, integrated circuit assemblies, integrated circuitry, power current switching methods, methods of forming a power semiconductor switching device, power conversion methods, power semiconductor switching device packaging methods, and methods of forming a power transistor are described. One exemplary aspect provides an integrated circuit assembly including a semiconductive substrate comprising a plurality of field effect transistors having electrically coupled sources and electrically coupled drains comprising regions of the substrate adjacent to a surface of the substrate, and wherein the electrically coupled sources and the electrically coupled drains are collectively configured to conduct power currents in excess of one Ampere; and a package having a plurality of source contacts and a plurality of drain contacts configured to couple with the electrically coupled sources and the electrically coupled drains of the semiconductive substrate, and wherein the source contacts and the drain contacts are provided adjacent to the surface of the package.